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deep adj trench adj capacitor and word adj lineC1

	U	1	Document	ID	Issue Date	Pages	Title	Current OR	Current XRef
38	✓	✓	US 60402210 A	20000321	67	3F-square memory cell for gigabit memory applications	438/238	257/E27.126; 257/E27.121;	
39	✓	✓	US 6037194 A	20000314	37	Method for making a DRAM cell with grooved transfer	438.147	438.171	
40	✓	✓	US 6034389 A	20000307	69	Self-aligned diffused source vertical transistors with	257/301	257/306; 257/308;	
41	✓	✓	US 6033967 A	20000307	8	Method for increasing capacitance in DRAM	438/398	438/255	
42	✓	✓	US 6033957 A	20000307	70	1F square memory cell having vertical floating-gate	438/370	257/E27.103; 257/E29.119;	
43	✓	✓	US 6025245 A	20000215	7	Method of forming a trench capacitor with a sacrificial	438/366	438.143; 438.143;	
44	✓	✓	US 6016268 A	20000118	11	Three transistor multi-state dynamic memory cell for	365/149	365.147	
45	✓	✓	US 6013548 A	20000111	70	Self-aligned diffused source vertical transistors with	438/342	257/E27.121; 438.143;	
46	✓	✓	US 5998821 A	19991207	19	Dynamic ram structure having a trench capacitor	257/301	257/396; 257.311;	
47	✓	✓	US 5998820 A	19991207	16	Fabrication method and structure for a DRAM cell	257/106	257/396; 257.375;	
48	✓	✓	US 5998410 A	19991130	7	Multiplication of storage capacitance in memory cells	365/149	365.147	

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